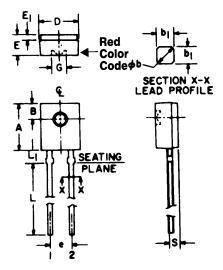


PLASTIC SILICON PHOTOTRANSISTOR

L14Q1





ST1335

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	110120
A	5.5 9	5.80	.220	.228	
В	1.78	NOM.	.070	NOM.	2
®b	.60	.75	.024	.030	1
b,	.51	NOM.	.020	NOM.	1
D	4.45	4.70	.175	.185	
E	2.41	2.67	.095	.105	
Ε,	.58	.69	.023	.027	
е	2.41	2.67	.095	.105	3
G	1.98	NOM.	.078	NOM.	
L	12.7	-	.500	-	
L,	1.40	1.65	.055	.065	
S	.83	.94	.033	.037	3

PACKAGE OUTLINE



511608

- NOTES: 1. TWO LEADS. LEAD CROSS SECTION DIMENSIONS UNCONTROLLED WITHIN 1.27mm (.050") OF SEATING PLANE.
- CENTERLINE OF ACTIVE ELEMENT LOCATED WITHIN .25mm (.010") OF TRUE POSITION.
 AS MEASURED AT THE SEATING PLANE.
- 4. INCH DIMENSIONS DERIVED FROM MILLIMETERS.

DESCRIPTION

The L14Q1 is a silicon phototransister encapsulated is a clear, wide angle, sidelooker package.

FEATURES

- Good optical to mechanical alignment
- Mechanically and wavelength matched to the F5F LED
- Plastic package with a color stripe for easy recognition from LED



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ABSOLUTE MAXIMUM RATINGS (T _A = 25°C Unless Otherwise Specified)					
Storage Temperature					
Soldering: Lead Temperature (Iron) Lead Temperature (Flow)	240°C for 5 sec. ^(2,3,4,5)				
Collector-Emitter Breakdown Voltage Emitter-Collector Breakdown Voltage Power Dissipation	6 Volts				

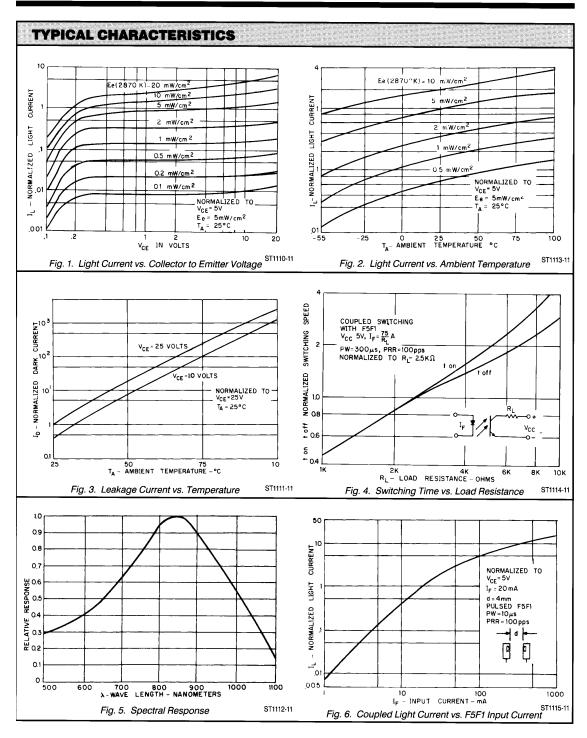
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
Collector-Emitter Breakdown	BV _{CEO}	30			V	$I_c = 10 \text{ mA}, \text{ Ee} = 0$
Emitter-Collector Breakdown	BV _{ECO}	6.0		_	V	$I_{e} = 100 \ \mu A, Ee = 0$
Collector-Emitter Leakage	I _{CEO}	_		100	nA	$V_{ce} = 25 V$, Ee = 0
Reception Angle at 1/2 Sensitivity	Θ		±35		Degrees	
On-State Collector Current	C(ON)	1.0		_	mA	$Ee = 1.5 \text{ mW/cm}^2$, $V_{CE} = 5 V^{(6.7)}$
Turn-On Time	t _{on}		8		μS	$I_{\scriptscriptstyle F}=30~mA,V_{\scriptscriptstyle CC}=5~V,R_{\scriptscriptstyle L}=2.5~K\Omega$
Turn-Off Time	t _{off}		50		μS	$I_c = 30$ mA, $V_{cc} = 5$ V, $R_L = 2.5$ KΩ
Saturation Voltage		_		0.40	V	$I_c = .5 \text{ mA}, \text{ Ee} = .60 \text{ mW/cm}^{2(6,7)}$

NOTES

Derate power dissipation linearly 2.00mW/°C above 25°C ambient.
RMA flux is recommended.
Methanol or Isopropyl alcohols are recommended as cleaning agents.
Soldering iron tip ¼s" (1.6 mm) minimum from housing.
As long as leads are not under any stress or spring tension.
Light source is a GaAs LED emitting light at a peak wavelength of 940 nm.
Figure 1 and figure 2 use light source of tungsten lamp at 2870°K color temperature. A GaAs source of 3.0 mW/cm² is approximately equivalent to a tungsten source, at 2870°K, of 10 mW/cm².



PLASTIC SILICON PHOTOTRANSISTOR





HERMETIC SILICON PHOTOTRANSISTOR

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- A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.